



STH275N8F7-2AG Information



For Reference Only

Part Number STH275N8F7-2AG Manufacturer STMicroelectronics

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 80V 180A H2PAK-2 **Package** TO-263-3, D2Pak (2 Leads + Tab) Variant

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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STH275N8F7-2AG Specifications

Manufacturer Part Number STH275N8F7-2AG Manufacturer STMicroelectronics Category Discrete Semiconductor Products Package TO-263-3, D2Pak (2 Leads + Tab) Variant Series Automotive, AEC-Q101, STripFET? F7 FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 80V Current - Continuous Drain (Id) @ 25°C 180A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4.5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 193nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 13600pF @ 50V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 315W (Tc) Rds On (Max) @ Id, Vgs 2.1 mOhm @ 90A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package H2Pak-2 Package / Case TO-263-3, D2Pak (2 Leads + Tab) Variant		
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FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)80VCurrent - Continuous Drain (Id) @ 25°C180A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4.5V @ 250μAGate Charge (Qg) (Max) @ Vgs193nC @ 10VInput Capacitance (Ciss) (Max) @ Vds13600pF @ 50VVgs (Max)±20VFET Feature-Power Dissipation (Max)315W (Tc)Rds On (Max) @ Id, Vgs2.1 mOhm @ 90A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageH2Pak-2Package / CaseTO-263-3, D2Pak (2 Leads + Tab) Variant	Package	TO-263-3, D2Pak (2 Leads + Tab) Variant
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)80VCurrent - Continuous Drain (Id) @ 25°C180A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4.5 V @ 250μAGate Charge (Qg) (Max) @ Vgs193nC @ 10VInput Capacitance (Ciss) (Max) @ Vds13600pF @ 50VVgs (Max)±20VFET Feature-Power Dissipation (Max)315W (Tc)Rds On (Max) @ Id, Vgs2.1 mOhm @ 90A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageH2Pak-2Package / CaseTO-263-3, D2Pak (2 Leads + Tab) Variant	Series	Automotive, AEC-Q101, STripFET? F7
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Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 2.1 mOhm @ 90A, 10V Operating Temperature Supplier Device Package Package / Case 180A (Tc) 190P 190P	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 4.5V @ 250μA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case TO-263-3, D2Pak (2 Leads + Tab) Variant	Drain to Source Voltage (Vdss)	80V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Surplier Device Package Package / Case 4.5V @ 250μA 193nC @ 10V 13600pF @ 50V ±20V FET Feature - - Surface Mount Surplier Device Package TO-263-3, D2Pak (2 Leads + Tab) Variant	Current - Continuous Drain (Id) @ 25°C	180A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 13600pF @ 50V Vgs (Max) ±20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 2.1 mOhm @ 90A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case TO-263-3, D2Pak (2 Leads + Tab) Variant	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 2.1 mOhm @ 90A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package H2Pak-2 Package / Case TO-263-3, D2Pak (2 Leads + Tab) Variant	Vgs(th) (Max) @ Id	4.5V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)315W (Tc)Rds On (Max) @ Id, Vgs2.1 mOhm @ 90A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageH2Pak-2Package / CaseTO-263-3, D2Pak (2 Leads + Tab) Variant	Gate Charge (Qg) (Max) @ Vgs	193nC @ 10V
FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 2.1 mOhm @ 90A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package H2Pak-2 Package / Case TO-263-3, D2Pak (2 Leads + Tab) Variant	Input Capacitance (Ciss) (Max) @ Vds	13600pF @ 50V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 2.1 mOhm @ 90A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package H2Pak-2 Package / Case TO-263-3, D2Pak (2 Leads + Tab) Variant	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs2.1 mOhm @ 90A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageH2Pak-2Package / CaseTO-263-3, D2Pak (2 Leads + Tab) Variant	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package H2Pak-2 Package / Case TO-263-3, D2Pak (2 Leads + Tab) Variant	Power Dissipation (Max)	315W (Tc)
Mounting Type Surface Mount Supplier Device Package H2Pak-2 Package / Case TO-263-3, D2Pak (2 Leads + Tab) Variant	Rds On (Max) @ Id, Vgs	2.1 mOhm @ 90A, 10V
Supplier Device Package H2Pak-2 Package / Case TO-263-3, D2Pak (2 Leads + Tab) Variant	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-263-3, D2Pak (2 Leads + Tab) Variant	Mounting Type	Surface Mount
	Supplier Device Package	H2Pak-2
Report errors?	Package / Case	TO-263-3, D2Pak (2 Leads + Tab) Variant
		Report errors?

STH275N8F7-2AG Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

STH275N8F7-2AG Payment Methods



















STH275N8F7-2AG Shipping Methods













If you have any question about STH275N8F7-2AG, please do not hesitate to contact us!

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